Claims

1. Bipolar transistor, with
an emitter area (3) which can be contacted electrically via an emitter electrode (1);
a base area (4) which can be contacted electrically via a base electrode (2);
a collector area (5) which can be contacted electrically via a collector electrode;
wherein at least one electrode of the emitter, base and collector electrodes (1, 2) is a polysilicon layer, into which doping is inserted,
characterized in that
into the at least one electrode, in addition to the doping, impurity atoms with a density of 10^{19} - 10^{21} cm^{-3} are inserted, the impurity atoms being C, P or Ar atoms.

2. Bipolar transistor according to Claim 1,
characterized in that
the polysilicon layer is doped with boron atoms.

3. Bipolar transistor according to Claim 2,
characterized in that
the concentration of the boron atoms is chosen to be greater than 5×10^{20} cm^{-3}.

4. Bipolar transistor according to one of the preceding claims,
characterized in that
the at least one electrode (1, 2) consists of polycrystalline silicon-germanium.

5. Bipolar transistor according to one of the preceding claims,
characterized in that
the at least one electrode is the base electrode (2).

6. Bipolar transistor according to one of the preceding claims,
characterized in that
the bipolar transistor is a self-aligned bipolar transistor.